DOCUMENT CHANGE REQUEST

DCR number 1582	Changes required for: General	Originator: Steve Thacker
Date: 2023/09/12	Date sent: 2023/06/28	Organisation: ESCC Executive Secretariat
Status: IMPLEMENTED		

Title:	TRANSISTORS, POWER, MOSFET, N CHANNEL, RAD-HARD BASED ON TYPES BUY06CS35J-01,		
Number:	5205/032	Issue:	2

Other documents affected:

Page:

Various; see attached

Paragraph:

Various; see attached & below

Original wording:

As per 5205/032 issue 2

Proposed wording:

Amend, for Variant 06 only, the maximum Static Drain-to-Source On Resistance, rDS(on), throughout this specification; to be as follows (see attached for details, with changes highlighted yellow):
a) In Para. 1.4.2, 2.5.1, 2.6, 2.7, 2.11.2:
Variant 06: change maximum limit for rDS(on) to be 7mohm (was 6.5mohm)

b) In Para. 2.5.2:
Variant 06: change maximum limit for rDS(on) to be 10.5mohm (was 10mohm)

Justification:

This DCR is raised on behalf of Manufacturer Infineon.

Infineon stated that, as previously discussed with ESA/Tesat/DLR, this marginal increase in maximum rDS(on) is required for the new (in 2023) Variant 06 due to:
"a shift of the RDSon distribution towards higher values (for new Variant 06 only). However we (Infineon) do not see any impact on the reliability of the device".

Attachments:
escc5205032iss_draft_3a_for_review.docx
Modifications:
N/A
Approval signature:

Date signed:
2023-09-12